

# **TN03N40SA**

## **N-Channel Enhancement Mode Power MOSFET**

#### **Features**

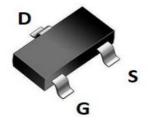
- $\bullet \;\;$  Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Halogen-free; RoHS-compliant
- · Pb-free plating

### **Applications**

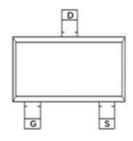
- Load Switch
- PWM Application
- Power Management

## **Product Summary**

Parameters	Value	Unit
$V_{DSS}$	40	V
$V_{GS(th)\_Typ}$	2.0	V
I <sub>D</sub> (@V <sub>GS</sub> =10V)	4	Α
$R_{DS(ON)\_Typ}(@V_{GS}=10V$	30	mΩ
$R_{DS(ON)\_Typ}(@V_{GS}=4.5V$	40	mΩ

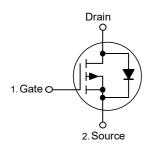


**SOT-23 Top View** 



Pin Assignment

## **Schematic Diagram**



### **Ordering Information**

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
TN03N40SA	03N40	3	Tape&Reel	SOT-23	3000	120000

## **Absolute Maximum Ratings** (@ T<sub>A</sub> = 25°C unless otherwise specified)

			,	
Symbol	Parameter		Value	Unit
V <sub>DS</sub>	Drain-to-Source Voltage	)	40	V
$V_{GS}$	Gate-to-Source Voltage	,	±20	V
,	Continuous Proin Current	T <sub>A</sub> = 25°C	3.9	۸
ID	Continuous Drain Current	$T_A = 100^{\circ}C$	2.4	— A
I <sub>DM</sub>	Pulsed Drain Current (1)	•	Refer to Fig.4	А
В	Dower Dissinction	T <sub>A</sub> = 25°C	1.1	10/
P <sub>D</sub>	Power Dissipation	$T_A = 100^{\circ}C$	0.4	w
T <sub>J</sub> , T <sub>STG</sub>	Junction & Storage Temperatur	e Range	-55 to 150	°C

### **Thermal Characteristics**

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(2)</sup>	166	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	114	C/VV

## **Electrical Characteristics** (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics			ļ		!
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 0V, V_{GS} = 40V$	-	-	1.0	μА
I <sub>GSS</sub>	Gate-Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	±100	nA
On Cha	racteristics					!
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.4	2.0	2.6	V
D	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10V, I_{D} = 4A$	-	30	39	mΩ
$R_{DS(ON)}$	Static Drain-Source ON-Resistance	$V_{GS} = 4.5V, I_D = 3A$	-	40	52	mΩ
Dynami	ic Characteristics					
$R_{g}$	Gate Resistance	f = 1MHz	-	2.3	-	Ω
$C_{iss}$	Input Capacitance	\/	383	536	723	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 20V,$ $f = 1MHz$	30	42	57	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 11/11/2	24	33	45	pF
Qg	Total Gate Charge	V 0. 45V	-	11	-	nC
$Q_{gs}$	Gate Source Charge	$V_{GS} = 0 \text{ to } 4.5V$ $V_{DS} = 20V, I_D = 3A$	-	2.2	-	nC
$Q_gd$	Gate Drain("Miller") Charge	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 0/1	-	2	-	nC
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On DelayTime		-	4.6	-	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10V, V_{DD} = 20V$	-	2	-	ns
t <sub>d(off)</sub>	Turn-Off DelayTime	$I_D = 3A, R_{GEN} = 3\Omega$	-	45	-	ns
t <sub>f</sub>	Turn-Off Fall Time	1	-	355	-	ns
Body D	iode Characteristics					<b>!</b>
Is	Maximum Continuous Body Diode Forward	d Current	-	-	4	А
I <sub>SM</sub>	Maximum Pulsed Body Diode Forward Cur	rent	-	-	15	А
V <sub>SD</sub>	Body Diode Forward Voltage	$V_{GS} = 0V, I_{S} = 30A$	-		1.2	V
trr	Body Diode Reverse Recovery Time	1 20 4:/4+ 4004/:	-	8.5	-	ns
Qrr	Body Diode Reverse Recovery Charge	$I_F = 3A$ , di/dt = 100A/us	-	3.8	-	nC

Notes:

- 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
- 2.  $R_{\theta JA}$  is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
- 3.  $R_{\theta JA}$  is measured with the device mounted on a 1inch  $^{\!2}$  pad of 2oz copper FR4 PCB.
- 4. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%.

# **Typical Performance Characteristics**

Figure 1: Power De-rating 1.2 P<sub>D</sub>(W) Multiplier 9.0 9.0 9.0 0.2 0 0 25 75 100 125 150  $T_A$ (°C) Ambient Temperature

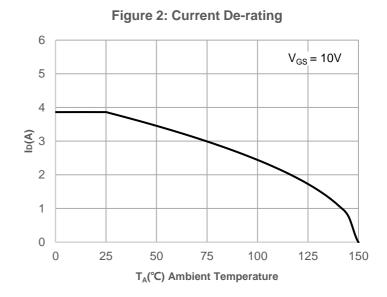
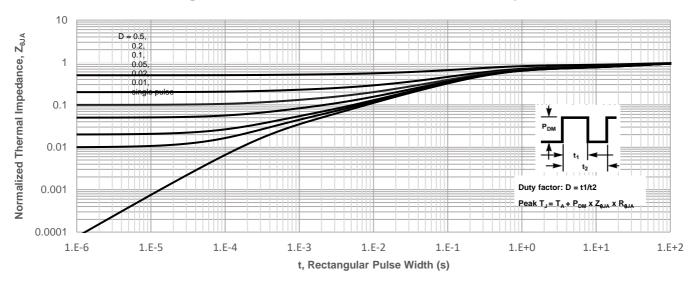
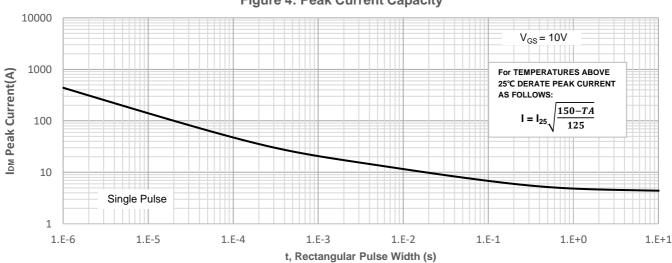


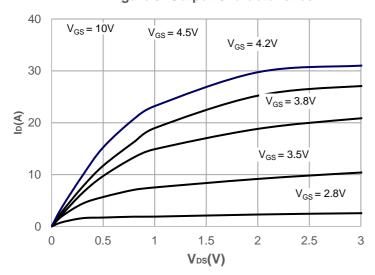
Figure 3: Normalized Maximum Transient Thermal Impedance





# **Typical Performance Characteristics**

**Figure 5: Output Characteristics** 



**Figure 6: Typical Transfer Characteristics** 

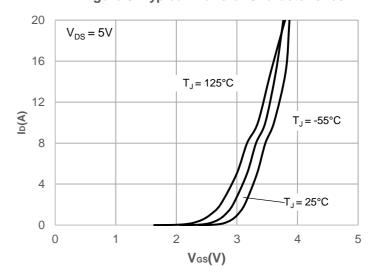
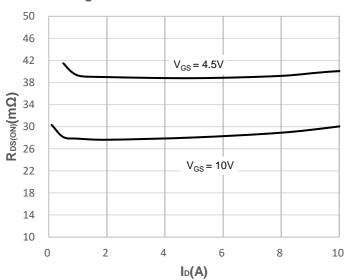
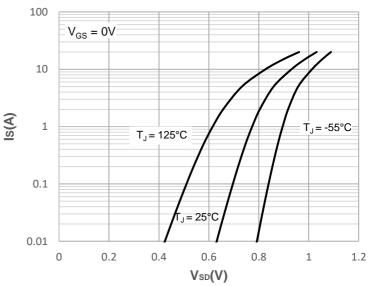


Figure 7: On-resistance vs. Drain Current



**Figure 8: Body Diode Characteristics** 



**Figure 9: Gate Charge Characteristics** 

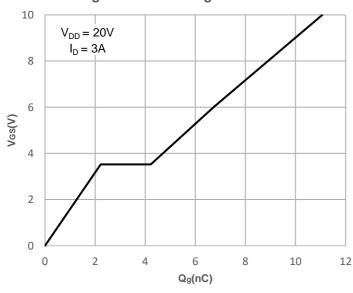
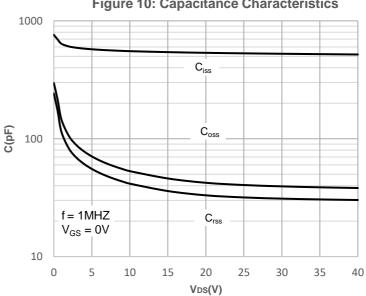


Figure 10: Capacitance Characteristics



# **Typical Performance Characteristics**

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

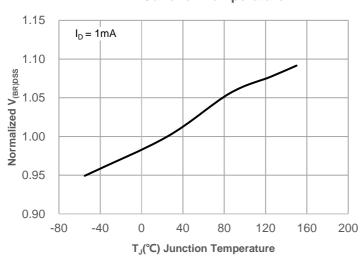


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

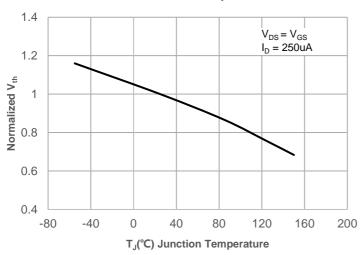


Figure 15: Maximum Safe Operating Area

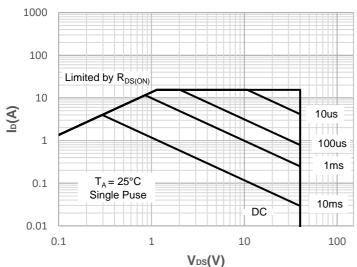


Figure 12: Normalized on Resistance vs. Junction Temperature

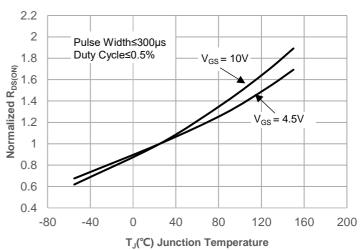
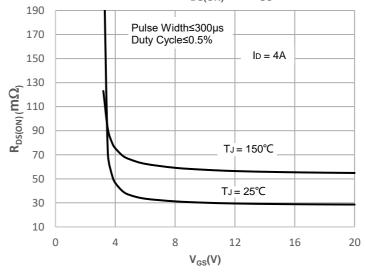


Figure 14: R<sub>DS(ON)</sub> vs. V<sub>GS</sub>



## **Test Circuit**

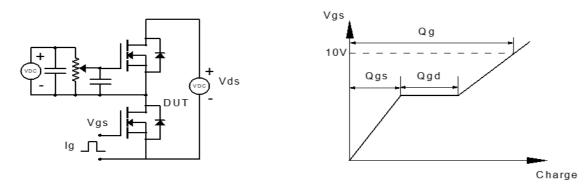


Figure 1: Gate Charge Test Circuit & Waveform

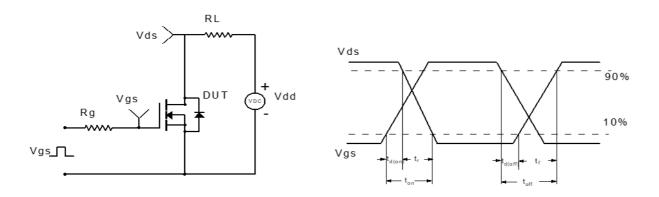


Figure 2: Resistive Switching Test Circuit & Waveform

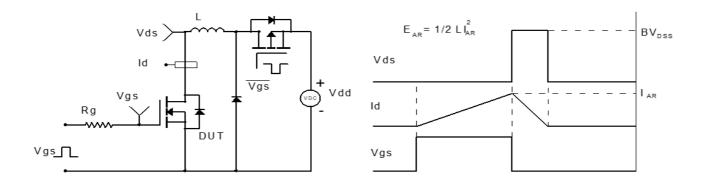


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

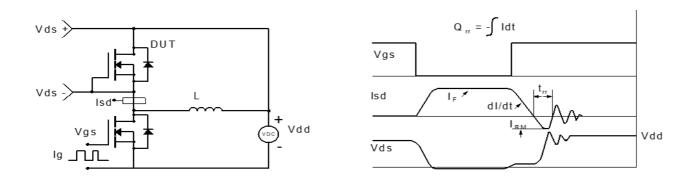
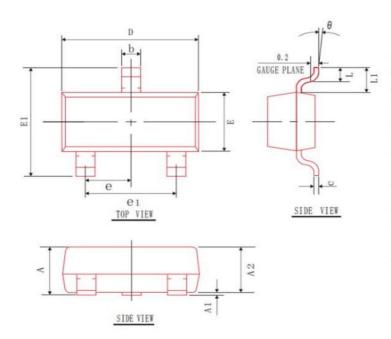


Figure 4: Diode Recovery Test Circuit & Waveform

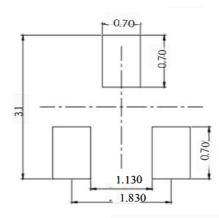
## Package Mechanical Data(SOT-23)



#### COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.90	1.05	1.20
A1	0.00	0.05	0.10
A2	0.90	1.00	1.10
b	0.30	0.40	0.50
С	0.08	0. 10	0.15
D	2.80	2.90	3.00
E	1. 20	1.30	1.40
E1	2. 30	2.40	2.50
L	0.30	0.40	0. 50
θ	0°	5°	10°
L1	0. 55 REF		
e	0. 95 BSC		
e i	1.90 REF		

#### Recommended Footprint



DIMENSIONS:MILLIMETERS

#### **Contact Information**

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For additional information, please contact your local Sales Representative.



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#### **Product Specification Statement**